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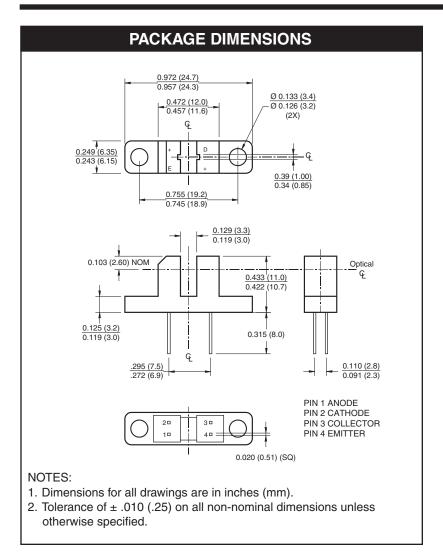


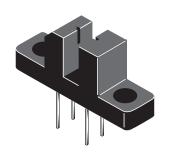


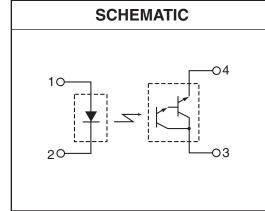




H21B1 H21B2 H21B3







DESCRIPTION

The H21B1, H21B2 and H21B3 consist of a gallium arsenide infrared emitting diode coupled with a silicon photodarlington in a plastic housing. The packaging system is designed to optimize the mechanical resolution, coupling efficiency, ambient light rejection, cost and reliability. The gap in the housing provides a means of interrupting the signal with an opaque material, switching the output from an "ON" to an "OFF" state.

FEATURES

- Opaque housing
- Low cost
- .035" apertures
- High I_{C(ON)}



H21B1 H21B2 H21B3

| Parameter | Symbol | Rating | Unit °C | |
|---|--------------------|--------------------|------------|--|
| Operating Temperature | T _{OPR} | -55 to +100 | | |
| Storage Temperature | T _{STG} | -55 to +100 | °C | |
| Soldering Temperature (Iron) ^(2,3 and 4) | T _{SOL-I} | 240 for 5 sec | °C | |
| Soldering Temperature (Flow) ^(2 and 3) | T _{SOL-F} | 260 for 10 sec | °C | |
| INPUT (EMITTER) | | | | |
| Continuous Forward Current | I _F | 50 | mA | |
| Reverse Voltage | V _R | 6 | V | |
| Power Dissipation ⁽¹⁾ | P _D | 100 m ¹ | | |
| OUTPUT (SENSOR) | | | | |
| Collector to Emitter Voltage | V _{CEO} | 30 | V | |
| Emitter to Collector Voltage | V _{ECO} | 6 | V | |
| Collector Current | I _C | 40 | mA | |
| Power Dissipation $(T_C = 25^{\circ}C)^{(1)}$ | P _D | 150 | mW | |

NOTES:

- 1. Derate power dissipation linearly 1.67 mW/°C above 25°C.
- 2. RMA flux is recommended.
- 3. Methanol or isopropyl alcohols are recommended as cleaning agents.
- 4. Soldering iron 1/16" (1.6 mm) minimum from housing.



H21B1

H21B2

H21B3

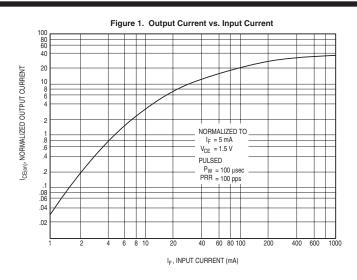
| PARAMETER | TEST CONDITIONS | SYMBOL | DEVICES | MIN | TYP | MAX | UNITS |
|-------------------------------------|---|----------------------|---------|-------------|-----|-----|------------------|
| INPUT (EMITTER) | | | | | | | |
| Forward Voltage | I _F = 60 mA | V _F | All | _ | _ | 1.7 | V |
| Reverse Breakdown Voltage | I _R = 10 μA | V _R | All | 6.0 | _ | _ | V |
| Reverse Leakage Current | V _R = 3 V | I _R | All | _ | _ | 1.0 | μΑ |
| OUTPUT (SENSOR) | | | | | | | |
| Emitter to Collector Breakdown | $I_F = 100 \mu A, E_e = 0$ | BV _{ECO} | All | 7.0 | _ | _ | V |
| Collector to Emitter Breakdown | $I_{C} = 1 \text{ mA}, E_{e} = 0$ | BV _{CEO} | All | 30 | _ | _ | V |
| Collector to Emitter Leakage | $V_{CE} = 25 \text{ V}, E_e = 0$ | I _{CEO} | All | _ | _ | 100 | nA |
| COUPLED On-State Collector Current | I _F = 2 mA, V _{CE} = 1.5 V | I _{C(ON)} | H21B1 | 0.5 | _ | _ | mA |
| | | | H21B2 | 1.0 | _ | _ | |
| | | | H21B3 | 2.0 | _ | _ | |
| | I _F = 5 mA, V _{CE} = 1.5 V | | H21B1 | 2.5 | _ | _ | |
| | | | H21B2 | 5.0 | _ | _ | |
| | | | H21B3 | 10 | _ | _ | |
| | I _F = 10 mA, V _{CE} = 1.5 V | | H21B1 | 7.5 | _ | _ | |
| | | | H21B2 | 14 | _ | _ | |
| | | | H21B3 | 25 | _ | _ | |
| Saturation Voltage | $I_F = 10 \text{ mA}, I_C = 1.8 \text{ mA}$ | \/ | All | _ | — | 1.0 | V |
| | $I_F = 60 \text{ mA}, I_C = 50 \text{ mA}$ | V _{CE(SAT)} | H21B1/2 | _ | _ | 1.5 | V |
| Turn-On Time | $I_F = 10 \text{ mA}, V_{CC} = 5 \text{ V},$ $R_L = 750\Omega$ | | All | _ | 45 | _ | μs |
| | $I_F = 60 \text{ mA}, V_{CC} = 5 \text{ V},$ $R_L = 75\Omega$ | t _{on} | All | _ | 7 | _ | |
| Turn-Off Time | $I_F = 10 \text{ mA}, V_{CC} = 5 \text{ V},$ $R_L = 750\Omega$ | | All | _ | 250 | _ | - µs |
| | $I_F = 60 \text{ mA}, V_{CC} = 5 \text{ V},$ $R_L = 75\Omega$ | Loff | All | _ | 45 | _ | |
| Turn-Off Time | $I_F = 10 \text{ mA}, V_{CC} = 5 \text{ V},$ $R_L = 750\Omega$ $I_F = 60 \text{ mA}, V_{CC} = 5 \text{ V},$ | t _{off} | All | _ _ _ | 250 | | - - - - |

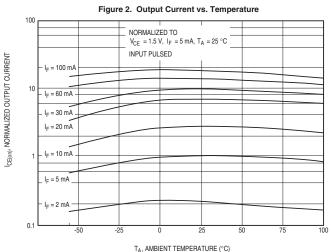


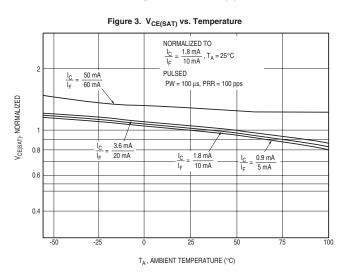
H21B1

H21B2

H21B3







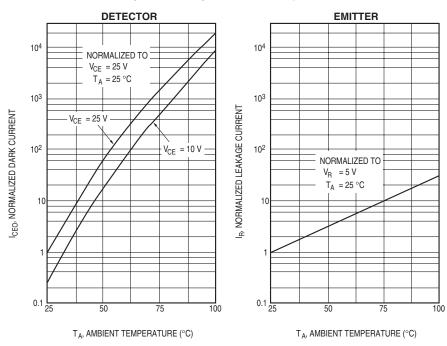


H21B1

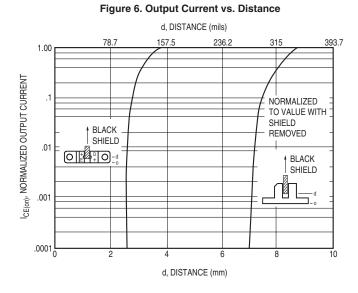
H21B2

H21B3

Figure 4. Leakage Current vs. Temperature



 R_L , LOAD RESISTANCE (Ω)





H21B1

H21B2

H21B3

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